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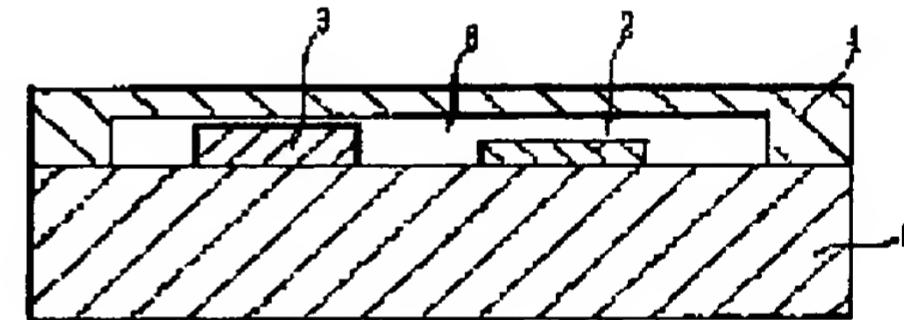
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(54) HIGH FREQUENCY INTEGRATED CIRCUIT ELEMENT**(57)Abstract:**

PURPOSE: To enable packaging by resin sealing by jointing a glass substrate provided with a space on the upper part of a dielectric thin film for which a surface acoustic wave element is manufactured and covering it.

CONSTITUTION: The surface acoustic wave element is provided in the dielectric thin film 2 formed on a silicon substrate 1, a high frequency amplifier element is provided in a semiconductor thin film 3 formed on the substrate 1 similarly and the glass substrate 4 is jointed on the substrate 1 so as to make the space 6 on the thin film 2. In such a manner, the surface acoustic wave element is physically and chemically protected by the space 6 provided by the substrate 4 jointed to the substrate 1 in a state where the space is formed on the upper part of the surface acoustic wave element. Since the resin of a package does not cover the surface of the thin film 2 where the surface acoustic wave element is formed even when it is packaged by the resin sealing, the function at the surface acoustic wave element is not hindered.



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